

an element isolation film formed such as to have a predetermined depth from a main surface of said semiconductor substrate, said element isolation film dividing the area from said main surface to said depth into a plurality of first regions;

first wells formed in said first regions, respectively; and

a second well formed in a second region deeper than each of said first wells in said semiconductor substrate, said second well being in contact with some of said first wells to provide electrical connection therebetween and not being in contact with said first wells adjacent to said some of said first wells,

wherein said first and second wells of said first and second regions on one side with reference to a predetermined boundary are of a first conductivity type, and said first wells on the other side are of a second conductivity type, and

wherein said second well is formed only on one side of said second region with reference to the predetermined boundary.

5. (Amended) A semiconductor device according to claim 1 wherein said second well is formed in a memory cell part in said second region.

15. (Twice Amended) A semiconductor device comprising:

a semiconductor substrate;

an element isolation film formed such as to have a predetermined depth from a main surface of said semiconductor substrate, said element isolation film dividing the area from said main surface to said depth into a plurality of first regions;

first wells formed in said first regions, respectively; and

a second well formed in a second region deeper than said first wells in said semiconductor substrate, said second well being in contact with a plurality of said first wells,

wherein said first and second wells of said first and second regions on one side with reference to a predetermined boundary are of a first conductivity type, and said first and second wells on the other side are of a second conductivity type, and

wherein the second well on one side of the predetermined boundary has a higher concentration than the first wells on said one side.

16. (Twice Amended) A semiconductor device comprising:

a semiconductor substrate;

a plurality of element isolation films formed such as to have a predetermined uniform depth from a main surface of said semiconductor substrate, said element isolation films dividing the area from said main surface to said depth into a plurality of first regions;

first wells formed in said first regions, respectively; and

a second well formed in a second region deeper than each of said first wells in said semiconductor substrate, said second well being in contact with some of said first wells,

wherein said first and second wells of said first and second regions on one side with reference to a predetermined boundary are of a first conductivity type, and said first wells on the other side are of a second conductivity type, and

wherein said second well is formed only on one side of said second region with reference to the predetermined boundary.

19. (Twice Amended) A semiconductor device according to claim 16 wherein said second well is formed in a memory cell part in said second region.

20. (Twice Amended) A semiconductor device according to claim 1 wherein a single element is formed in a single first region.

22. (Twice Amended) A semiconductor device according to claim 15 wherein a single element is formed in a single first region.